

## REPLACEMENT CLAIMS

a1 1. (Amended) A method of forming a copper damascene structure, said method comprising the steps of:

patterning a low-dielectric constant layer to form at least one opening through said low-dielectric constant layer;

Pub B1  
forming a tungsten nitride layer by atomic-layer deposition using sequential surface reactions, said tungsten nitride layer being in contact with said at least one opening; and

providing a copper layer in said at least one opening and in contact with said tungsten nitride layer, wherein said copper layer is selectively deposited by chemical vapor deposition.

Sub C1  
~~2. (Amended) The method of claim 1, wherein said low-dielectric constant layer includes a material selected from the group consisting of methylsilsequiazane, polyimide, spin-on-polymers, flare, polyarylethers, parylene, polytetrafluoroethylene, benzocyclobutene, fluorinated silicon oxide, and hydrogen silsesquioxane.~~

a2 Sub C2  
~~11. (Amended) The method of claim 1, wherein said copper layer is selectively deposited at a temperature of about 300°C to about 400°C.~~

a3 14. (Amended) A method of forming a copper damascene structure, said method comprising the steps of:

Pub B2  
patterning a low-dielectric constant layer to form at least one opening through said low-dielectric constant layer;

a3  
cont.  
B2  
vml

forming a tungsten nitride layer by atomic-layer deposition using sequential surface reactions, said tungsten nitride layer being in contact with said at least one opening;  
and

providing a copper layer in said at least one opening, wherein said copper layer is formed by electroless deposition.

---